

YJ Planar Schottky Barrier Diode Die Specification

150V 3A, 55mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB055H150SS-280A

Main Products Characterstics

Maximum Ratings			Static Electrical Characteristics (Ta = 25°C)			
					Value	
					Spec	Typical
					155 V	170V
(tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	80 A	Maximum forward voltage drop		V _F	0.85V
			I _F = 3 A			
Storage temperature range	T _{stg}	-50 to +175 °C	≤ 2%			0.79V
Maximum operating junction temperature	T _j	175 °C			5uA	0.2uA

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	50 Mils
Active Area	46 Mils
Top Metal	Ag
Back Metal	
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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